

**30V DUAL P-CHANNEL ENHANCEMENT MODE MOSFET**

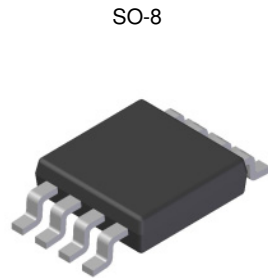
**Product Summary**

$V_{(BR)DSS}$	$R_{DS(on)}$ Max	$I_D$ $T_A = 25^\circ C$ (Notes 4 & 6)
-30V	25m $\Omega$ @ $V_{GS} = -10V$	-8.3A
	41m $\Omega$ @ $V_{GS} = -4.5V$	-6.5A

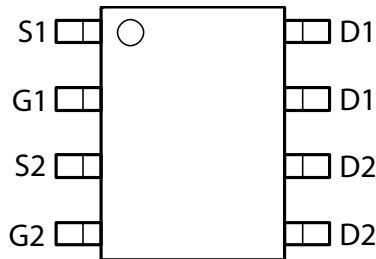
**Description and Applications**

This MOSFET has been designed to minimize the on-state resistance and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

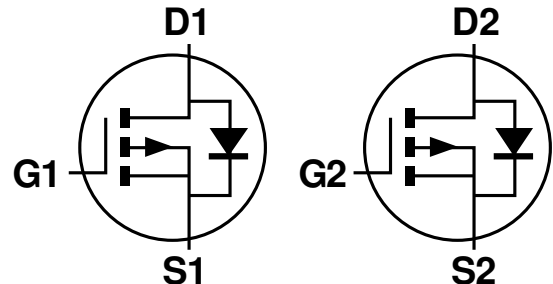
- DC-DC Converters
- Power Management functions
- Disconnect Switches
- Motor control



Top View



Top View



Equivalent Circuit

**Features and Benefits**

- Low on-resistance
- Fast switching speed
- Low threshold
- Low gate drive
- "Lead-Free", RoHS compliant (Note 1)
- Halogen and Antimony Free. "Green" Device (Note 1)
- Qualified to AEC-Q101 Standards for High Reliability

**Mechanical Data**

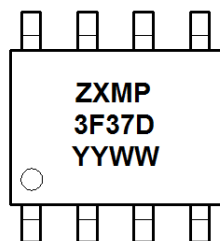
- Case: SO-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0 (Note 1)
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish; Solderable per MIL-STD-202, Method 208
- Weight: 0.074 grams (approximate)

**Ordering Information** (Note 1)

Product	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
ZXMP3F37DN8TA	ZXMP3F37D	7	12	500

Notes: 1. Diodes, Inc. defines "Green" products as those which are RoHS compliant and contain no halogens or antimony compounds; further information about Diodes Inc.'s "Green" Policy can be found on our website. For packaging details, go to our website.

**Marking Information**



ZXMP3F37D = Product Type Marking Code  
 YYWW = Date Code Marking  
 YY = Year (ex: 11 = 2011)  
 WW = Week (01 - 53)

**Maximum Ratings** @T<sub>A</sub> = 25°C unless otherwise specified

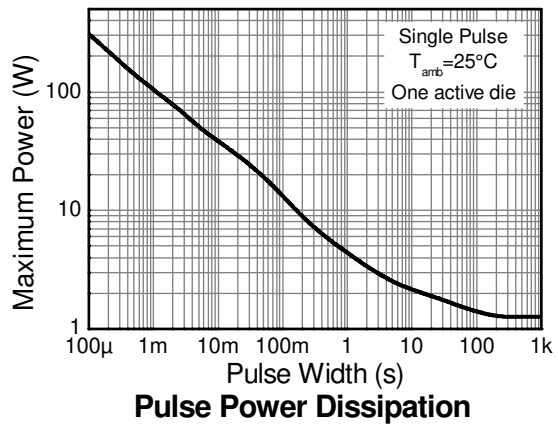
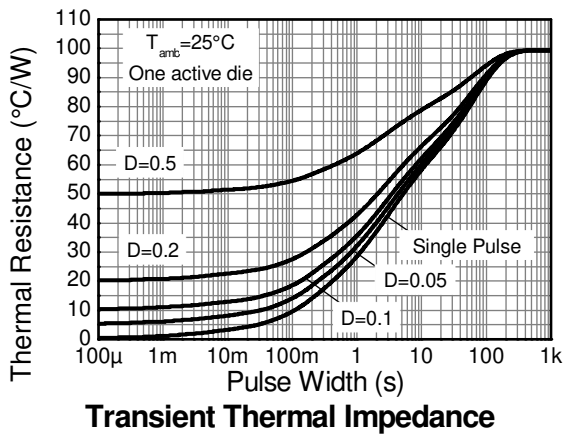
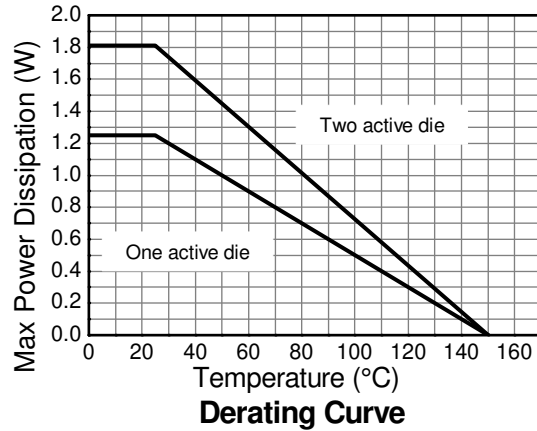
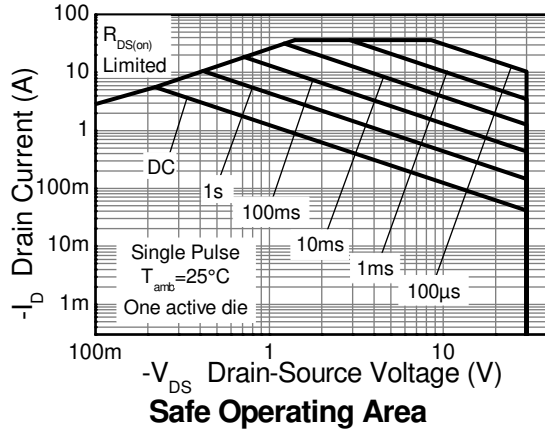
Characteristic			Symbol	Value	Unit
Drain-Source voltage			V <sub>DSS</sub>	-30	V
Gate-Source voltage			V <sub>GS</sub>	±20	V
Continuous Drain current	V <sub>GS</sub> = -10V	(Notes 3 & 5)	I <sub>D</sub>	-7.3	A
		T <sub>A</sub> = 70°C (Notes 3 & 5)		-5.9	
		(Notes 2 & 5)		-5.7	
		(Note 7)		-8.3	
Pulsed Drain current		(Notes 4)	I <sub>DM</sub>	-36	A
Continuous Source current (Body diode)		(Notes 3)	I <sub>S</sub>	-3.5	A
Pulsed Source current (Body diode)		(Notes 4)	I <sub>SM</sub>	-36	A

**Thermal Characteristics** @T<sub>A</sub> = 25°C unless otherwise specified

Characteristic		Symbol	Value	Unit
Power dissipation Linear derating factor	(Notes 2 & 5)	P <sub>D</sub>	1.25	W mW/°C
			10.0	
	(Notes 2 & 6)		1.81	
			14	
	(Notes 3 & 5)		2.1	
			17	
Thermal Resistance, Junction to Ambient	(Notes 2 & 5)	R <sub>θJA</sub>	100	°C/W
	(Notes 2 & 6)		70	
	(Notes 3 & 5)		60	
Thermal Resistance, Junction to Lead	(Notes 2 & 7)	R <sub>θJL</sub>	46	°C/W
Operating and storage temperature range		T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

- Notes:
2. For a device surface mounted on 25mm x 25mm x 1.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions; the device is measured when operating in a steady-state condition.
  3. For a dual device surface mounted on FR4 PCB measured at t ≤ 10 sec.
  4. Repetitive rating on 25mm X 25mm FR4 PCB, pulsed with D = 0.02 and pulse width 300µs – pulse width limited by maximum junction temperature.
  5. For a dual device with one active die.
  6. For a device with two active die running at equal power.
  7. Thermal resistance from junction to solder-point (at the end of the drain lead).

**Thermal Characteristics**

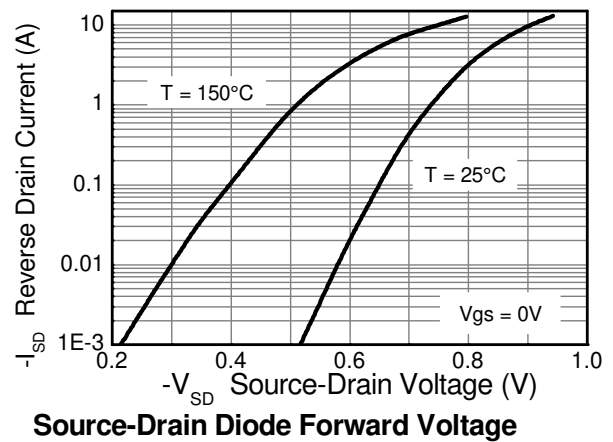
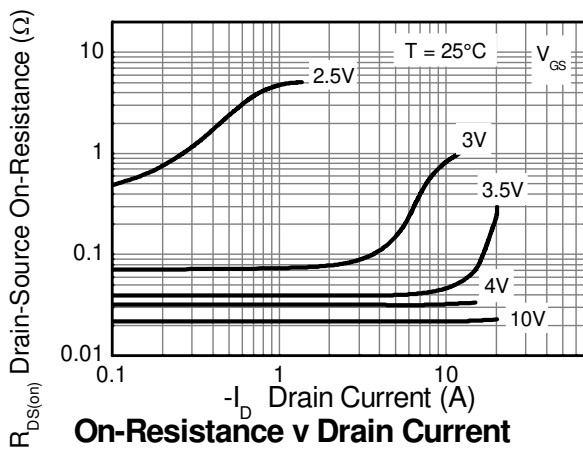
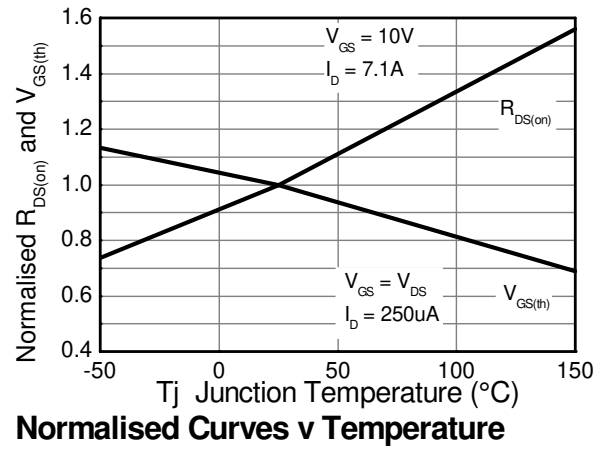
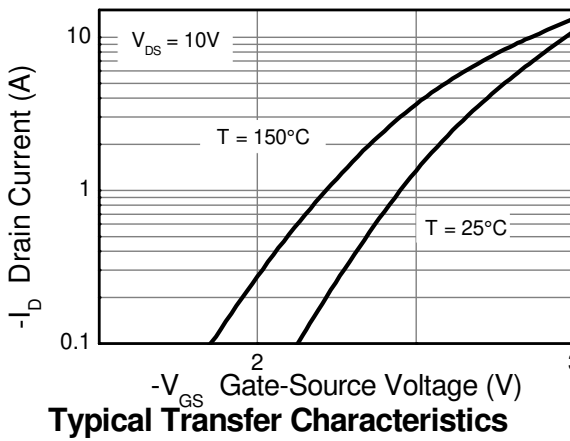
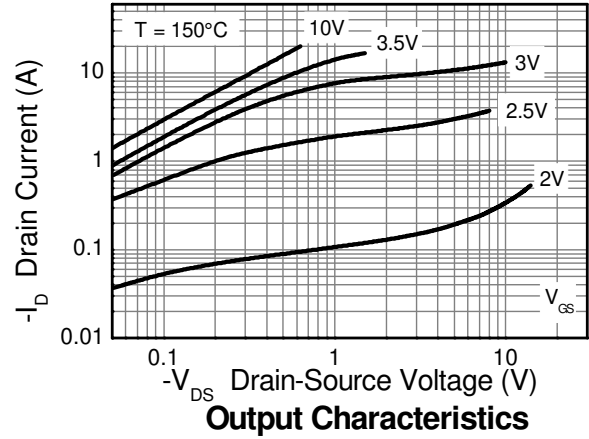
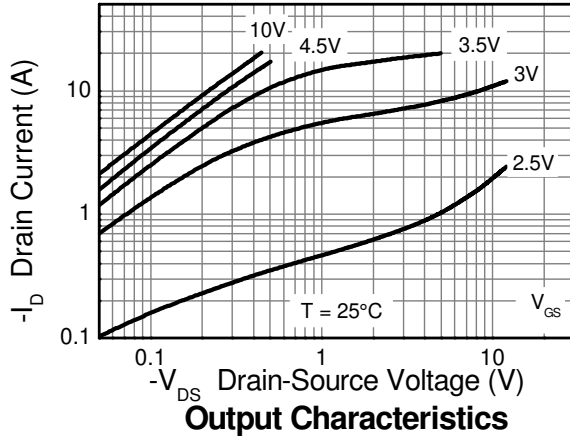


**Electrical Characteristics** @ $T_A = 25^\circ\text{C}$  unless otherwise specified

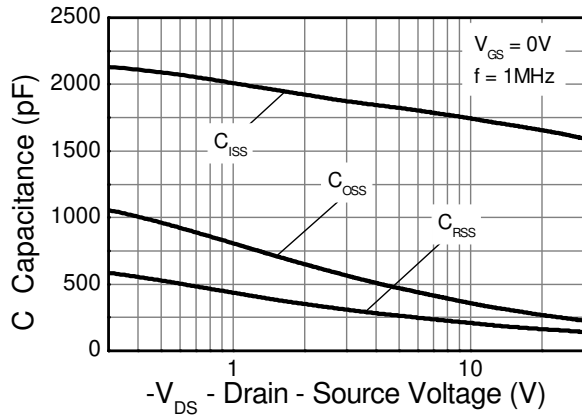
Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS</b>						
Drain-Source Breakdown Voltage	$BV_{DSS}$	-30	—	—	V	$I_D = -250\mu\text{A}, V_{GS} = 0\text{V}$
Zero Gate Voltage Drain Current	$I_{DSS}$	—	—	-0.5	$\mu\text{A}$	$V_{DS} = -30\text{V}, V_{GS} = 0\text{V}$
Gate-Source Leakage	$I_{GSS}$	—	—	$\pm 100$	nA	$V_{GS} = \pm 20\text{V}, V_{DS} = 0\text{V}$
<b>ON CHARACTERISTICS</b>						
Gate Threshold Voltage	$V_{GS(th)}$	-1.0	—	-3.0	V	$I_D = -250\mu\text{A}, V_{DS} = V_{GS}$
Static Drain-Source On-Resistance (Note 8)	$R_{DS(on)}$	—	—	25	m $\Omega$	$V_{GS} = -10\text{V}, I_D = -7.1\text{A}$
			—	41		$V_{GS} = -4.5\text{V}, I_D = -5.5\text{A}$
Forward Transconductance (Notes 8 & 9)	$g_{fs}$	—	18.6	—	S	$V_{DS} = -15\text{V}, I_D = -7.1\text{A}$
Diode Forward Voltage (Note 8)	$V_{SD}$	—	-0.8	-1.2	V	$I_S = -1.7\text{A}, V_{GS} = 0\text{V}$
Reverse recovery time (Note 9)	$t_{rr}$	—	16.2	—	ns	$I_S = -2.2\text{A}, di/dt = 100\text{A}/\mu\text{s}$
Reverse recovery charge (Note 9)	$Q_{rr}$	—	10	—	nC	
<b>DYNAMIC CHARACTERISTICS (Note 9)</b>						
Input Capacitance	$C_{iss}$	—	1678	—	pF	$V_{DS} = -15\text{V}, V_{GS} = 0\text{V}$ $f = 1\text{MHz}$
Output Capacitance	$C_{oss}$	—	303	—	pF	
Reverse Transfer Capacitance	$C_{rss}$	—	178	—	pF	
Total Gate Charge (Note 10)	$Q_g$	—	31.6	—	nC	$V_{GS} = -10\text{V}, V_{DS} = -15\text{V},$ $I_D = -7.1\text{A}$
Gate-Source Charge (Note 10)	$Q_{gs}$	—	4.3	—	nC	
Gate-Drain Charge (Note 10)	$Q_{gd}$	—	6.2	—	nC	
Turn-On Delay Time (Note 10)	$t_{D(on)}$	—	3.5	—	ns	$V_{DD} = -15\text{V}, V_{GS} = -10\text{V}$ $I_D = -1\text{A}, R_G \cong 6.0\Omega$
Turn-On Rise Time (Note 10)	$t_r$	—	4.9	—	ns	
Turn-Off Delay Time (Note 10)	$t_{D(off)}$	—	44	—	ns	
Turn-Off Fall Time (Note 10)	$t_f$	—	28	—	ns	

- Notes:
8. Measured under pulsed conditions. Pulse width  $\leq 300\mu\text{s}$ ; duty cycle  $\leq 2\%$
  9. For design aid only, not subject to production testing.
  10. Switching characteristics are independent of operating junction temperatures.

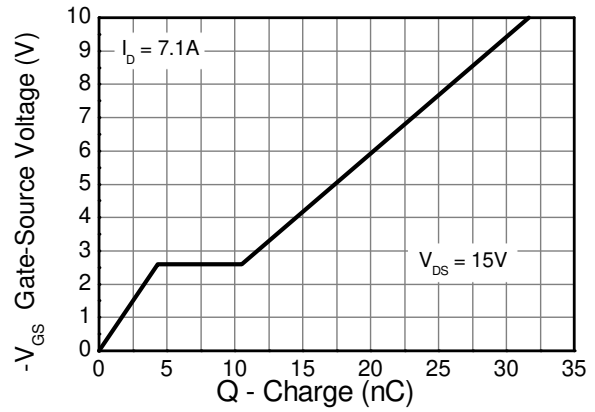
**Typical Characteristics**



**Typical Characteristics - continued**

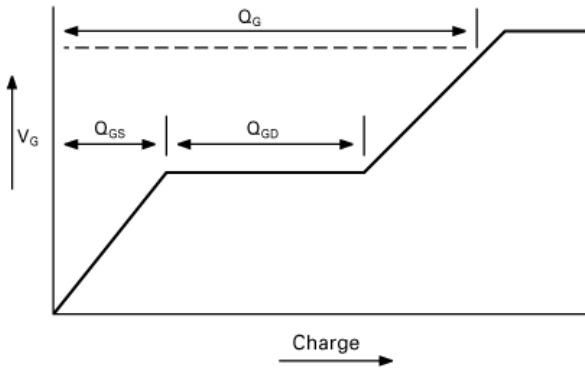


**Capacitance v Drain-Source Voltage**

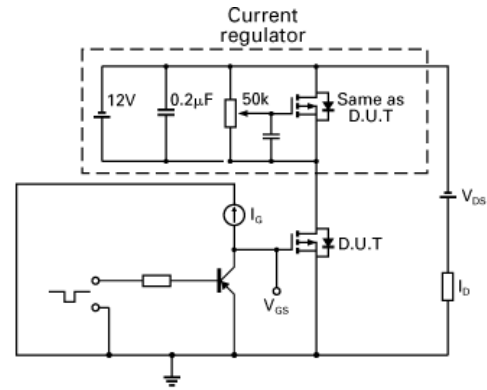


**Gate-Source Voltage v Gate Charge**

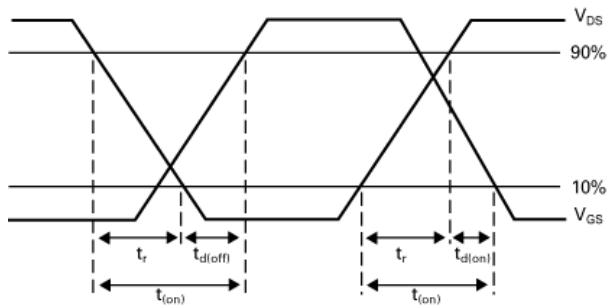
**Test Circuits**



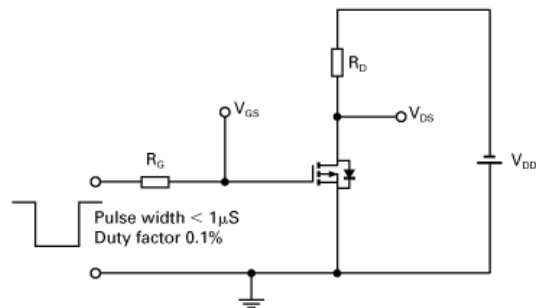
**Basic gate charge waveform**



**Gate charge test circuit**

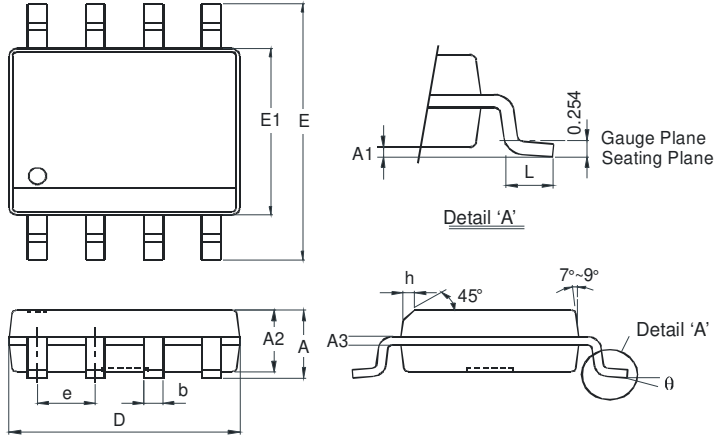


**Switching time waveforms**



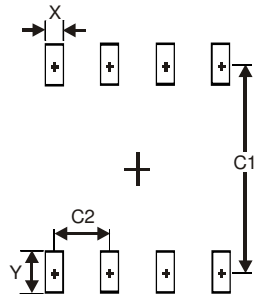
**Switching time test circuit**

**Package Outline Dimensions**



SO-8		
Dim	Min	Max
A	-	1.75
A1	0.10	0.20
A2	1.30	1.50
A3	0.15	0.25
b	0.3	0.5
D	4.85	4.95
E	5.90	6.10
E1	3.85	3.95
e	1.27 Typ	
h	-	0.35
L	0.62	0.82
θ	0°	8°
All Dimensions in mm		

**Suggested Pad Layout**



Dimensions	Value (in mm)
X	0.60
Y	1.55
C1	5.4
C2	1.27

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